NSN 5962-01-119-6665

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View Online at https://aerobasegroup.com/nsn/5962-01-119-6665
Body Length:
Between 0.745 inches and 0.755 inches
Body Width:
Between 0.245 inches and 0.252 inches
Body Height:
Between 0.115 inches and 0.125 inches
Maximum Power Dissipation Rating:
333.0 milliwatts
Operating Tempurature Range:
+0.0/+75.0 degrees celsius
Storage Tempurature Range:
-65.0/+150.0 degrees celsius
End Application:
Ts-3852 v2g e/i fscm 80058
Features Provided:
Monolithic and bipolar and expandable and positive outputs and w/enable and 3-state output
Inclosure Material:
Plastic
Inclosure Configuration:
Dual-in-line
Output Logic Form:
Transistor-transistor logic
Input Circuit Pattern:
6 input
Terminal Surface Treatment:
Solder
Voltage Rating And Type Per Characteristic:
-1.5 volts power source and 5.5 volts power source
Time Rating Per Chacteristic:
65.00 nanoseconds propagation delay time, low to high level output and 65.00 nanoseconds propagation delay time, high to low level
output
Memory Device Type:
Rom
Test Data Document:
50621-021-0005 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.;
excludes any specification, standard or other document that may be referenced in a basic governing drawing)
Terminal Type And Quantity:
16 printed circuit
Shelf Life:
N/a
Unit Of Measure:

Yes - demil/mli

Demilitarization:

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